CSD22205L –8V P 沟道 NexFET™ 功率 MOSFET

1 特性

- 低电阻
- 1.2mm × 1.2mm 小尺寸封装
- 扁平设计，高度为 0.35mm
- 无铅
- 栅源电压钳位
- 栅极 ESD 保护
- 符合 RoHS 标准
- 无卤素

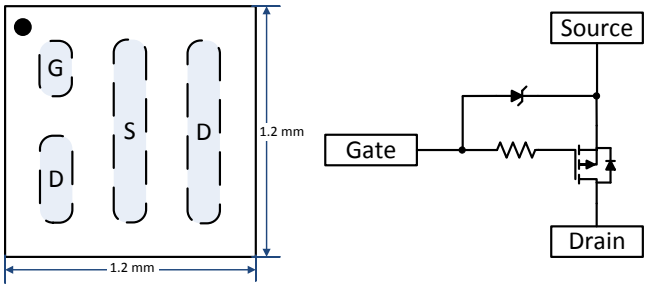
2 应用

- 电池管理
- 负载开关
- 电池保护

3 说明

该 –8V、8.2mΩ、1.2mm × 1.2mm 基板栅格阵列 (LGA) NexFET™器件旨在以超薄且具有出色散热特性的最小外形尺寸封装提供最低的导通电阻和栅极电荷。基板栅格阵列 (LGA) 封装是一种带有金属接触板（而非焊球）的器件芯片级封装。

顶视图和电路配置



产品概要

T_A = 25°C		值		单位
V_{DS}	漏源电压	–8		V
Q_g	总栅极电荷 (–4.5V)	6.5		nC
Q_{gd}	栅极电荷（栅极到漏极）	1.0		nC
$R_{DS(on)}$	漏源导通电阻	V_{GS} = –1.5V	30	mΩ
		V_{GS} = –1.8V	20	
		V_{GS} = –2.5V	11.5	
		V_{GS} = –4.5V	8.2	
$V_{GS(th)}$	阈值电压	–0.7		V

器件信息(1)

器件	数量	包装介质	封装	发货
CSD22205L	3000	7 英寸卷带	1.20mm × 1.20mm 基板栅格阵列封装	卷带封装
CSD22205LT	250			

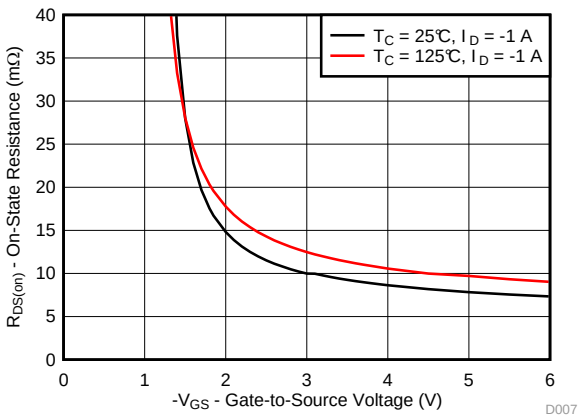
(1) 如需了解所有可用封装，请参阅数据表末尾的可订购产品附录。

绝对最大额定值

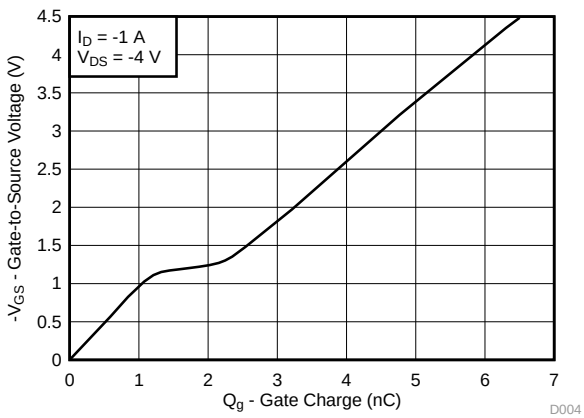
T_A = 25°C		值	单位
V_{DS}	漏源电压	–8	V
V_{GS}	栅源电压	–6	V
I_D	持续漏极电流(1)	–7.4	A
I_{DM}	脉冲漏极电流(2)	–71	A
P_D	功率耗散(1)	0.6	W
T_J、T_{stg}	工作结温、储存温度	–55 至 150	°C

(1) $R_{\theta JA}$ = 225°C/W（覆铜面积最小时的值）。
(2) 脉宽 ≤ 100µs，占空比 ≤ 1%。

$R_{DS(on)}$ 与 V_{GS} 之间的关系



$R_{DS(on)}$ 与 V_{GS} 之间的关系



目录

4 修订历史记录

Changes from Original (May 2017) to Revision A **Page**

- Changed the units for timing parameters from µs : to ns (nanoseconds) in the *Electrical Characteristics* table 3

5 Specifications

5.1 Electrical Characteristics

T_A = 25°C (unless otherwise stated)

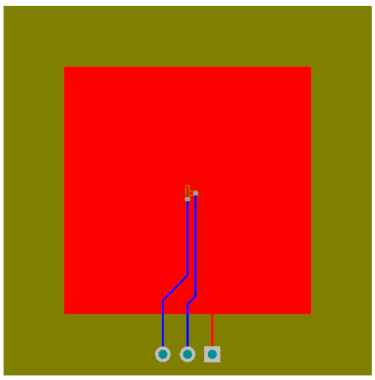
PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
STATIC CHARACTERISTICS						
BV_{DSS}	Drain-to-source voltage	V_{GS} = 0 V, I_D = –250 μA	–8			V
I_{DSS}	Drain-to-source leakage current	V_{GS} = 0 V, V_{DS} = –6.4 V			–100	nA
I_{GSS}	Gate-to-source leakage current	V_{DS} = 0 V, V_{GS} = –6 V			–100	nA
$V_{GS(th)}$	Gate-to-source threshold voltage	V_{DS} = V_{GS}, I_D = –250 μA	–0.4	–0.7	–1.05	V
$R_{DS(on)}$	Drain-to-source on-resistance	V_{GS} = –1.5 V, I_D = –0.2 A		30		mΩ
		V_{GS} = –1.8 V, I_D = –1 A		20	40	
		V_{GS} = –2.5 V, I_D = –1 A		11.5	15.0	
		V_{GS} = –4.5 V, I_D = –1 A		8.2	9.9	
g_{fs}	Transconductance	V_{DS} = –0.8 V, I_D = –1 A		10.4		S
DYNAMIC CHARACTERISTICS						
C_{ISS}	Input capacitance	V_{GS} = 0 V, V_{DS} = –4 V, f = 1 MHz		1070	1390	pF
C_{OSS}	Output capacitance			560	730	pF
C_{RSS}	Reverse transfer capacitance			190	250	pF
R_G	Series gate resistance			30		Ω
Q_g	Gate charge total (–4.5 V)	V_{DS} = –4 V, I_D = –1 A		6.5	8.5	nC
Q_{gd}	Gate charge gate-to-drain			1.0		nC
Q_{gs}	Gate charge gate-to-source			1.2		nC
$Q_{g(th)}$	Gate charge at V_{th}			0.7		nC
Q_{OSS}	Output charge	V_{DS} = –4 V, V_{GS} = 0 V		4.1		nC
$t_{d(on)}$	Turnon delay time	V_{DS} = –4 V, V_{GS} = –4.5 V, I_D = –1 A , R_G = 0 Ω		30		ns
t_r	Rise time			14		ns
$t_{d(off)}$	Turnoff delay time			70		ns
t_f	Fall time			32		ns
DIODE CHARACTERISTICS						
V_{SD}	Diode forward voltage	I_S = –1 A, V_{GS} = 0 V		–0.68	–1.0	V
Q_{rr}	Reverse recovery charge	V_{DS}= –4 V, I_F = –1 A, di/dt = 200 A/μs		16		nC
t_{rr}	Reverse recovery time			38		ns

5.2 Thermal Information

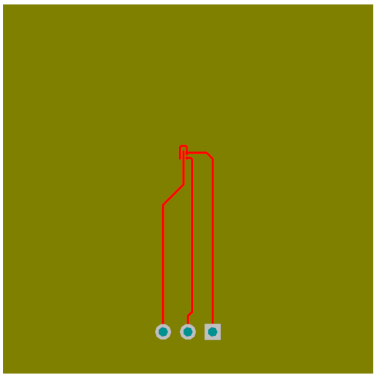
T_A = 25°C (unless otherwise stated)

THERMAL METRIC		MIN	TYP	MAX	UNIT
$R_{\theta JA}$	Junction-to-ambient thermal resistance(1)		75		°C/W
	Junction-to-ambient thermal resistance(2)		225		

(1) Device mounted on FR4 material with 1-in^2 (6.45-cm^2), 2-oz (0.071-mm) thick Cu.
(2) Device mounted on FR4 material with minimum Cu mounting area.



Typ $R_{\theta JA}$ =75°C/W when mounted on 1 in^2 of 2-oz Cu.



Typ $R_{\theta JA}$ = 225°C/W when mounted on minimum pad area of 2-oz Cu.

5.3 Typical MOSFET Characteristics

T_A = 25°C (unless otherwise stated)

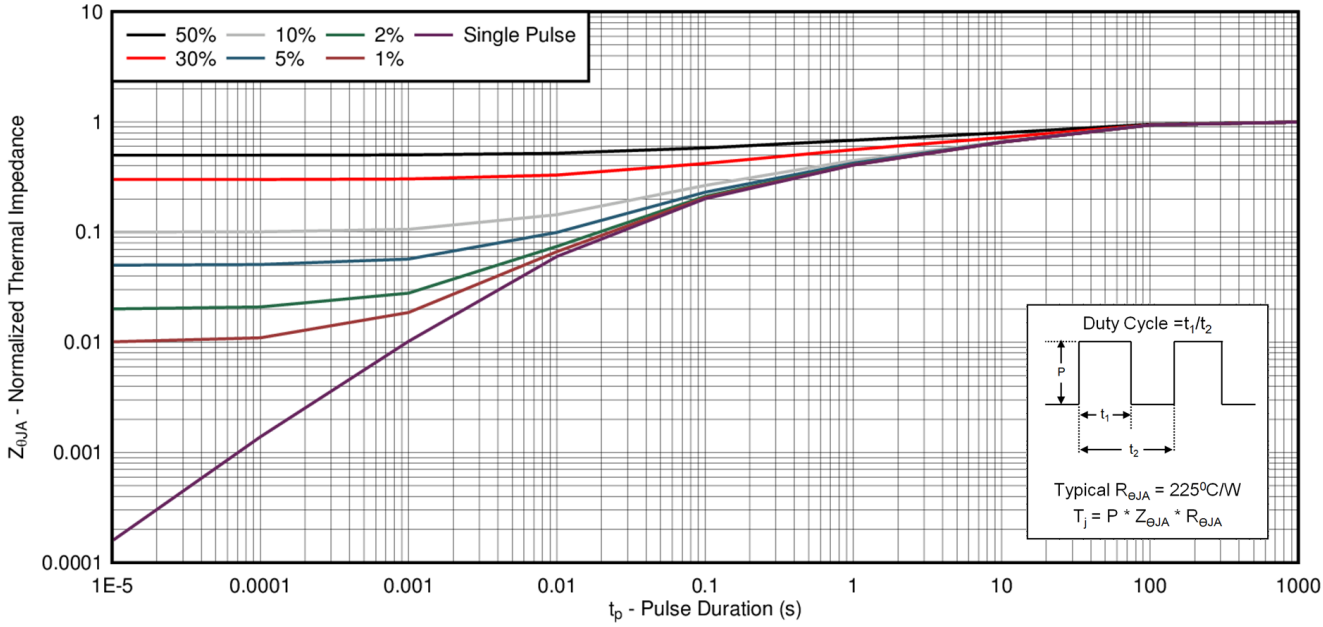


Figure 1. Transient Thermal Impedance

Typical MOSFET Characteristics (continued)

T_A = 25°C (unless otherwise stated)

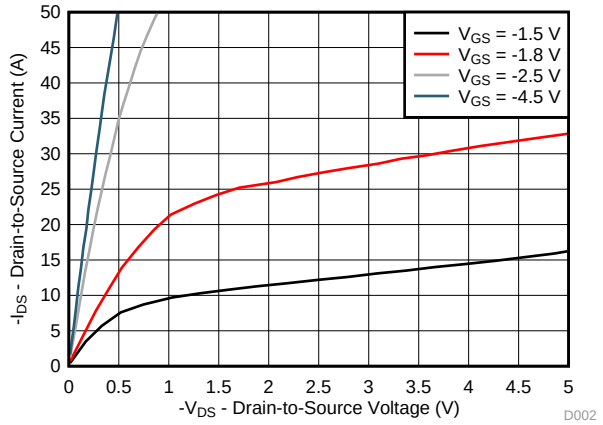


Figure 2. Saturation Characteristics

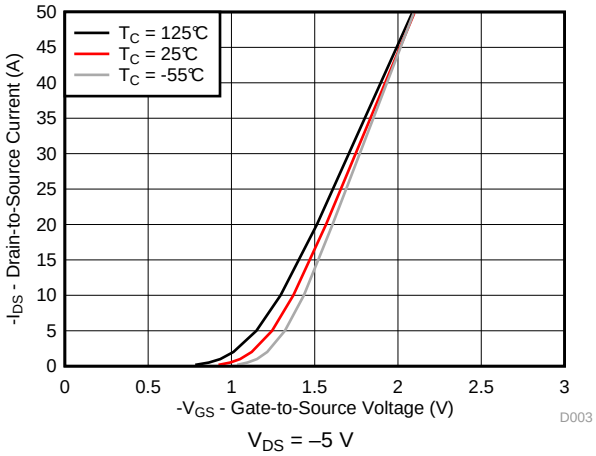


Figure 3. Transfer Characteristics

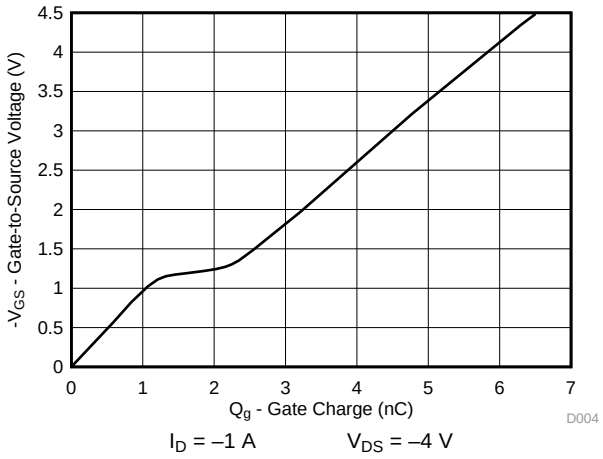


Figure 4. Gate Charge

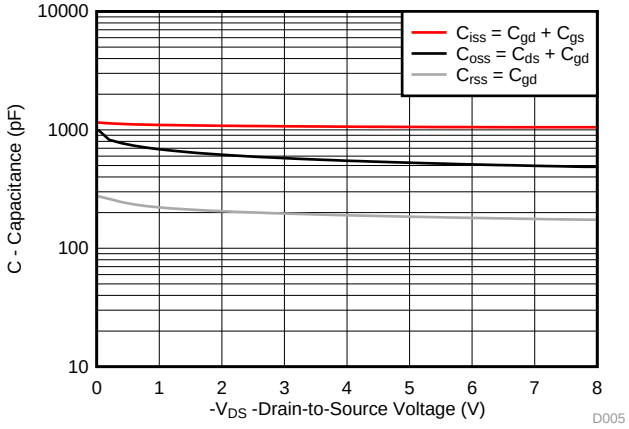


Figure 5. Capacitance

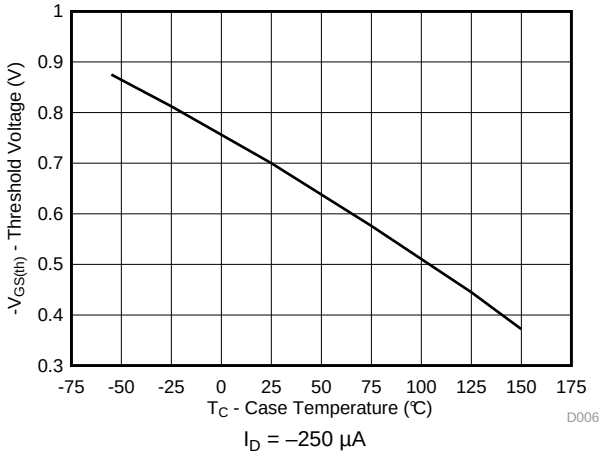


Figure 6. Threshold Voltage vs Temperature

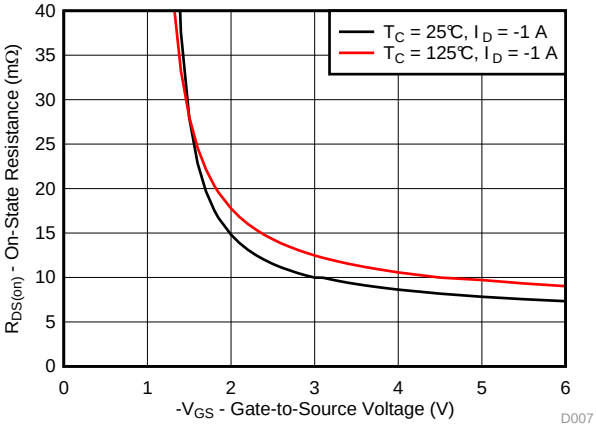
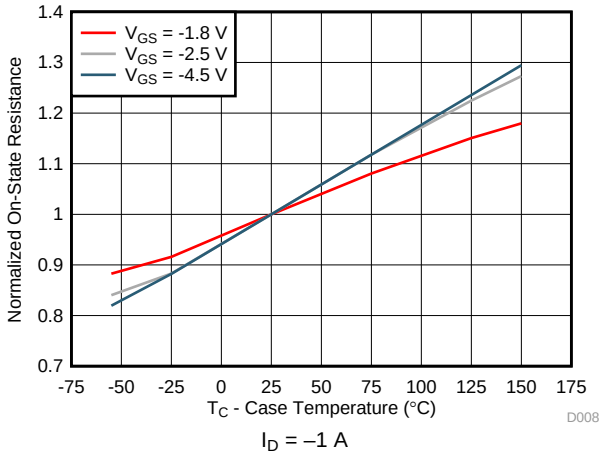


Figure 7. On-State Resistance vs Gate-to-Source Voltage

Typical MOSFET Characteristics (continued)

T_A = 25°C (unless otherwise stated)



I_D = –1 A

Figure 8. Normalized On-State Resistance vs Temperature

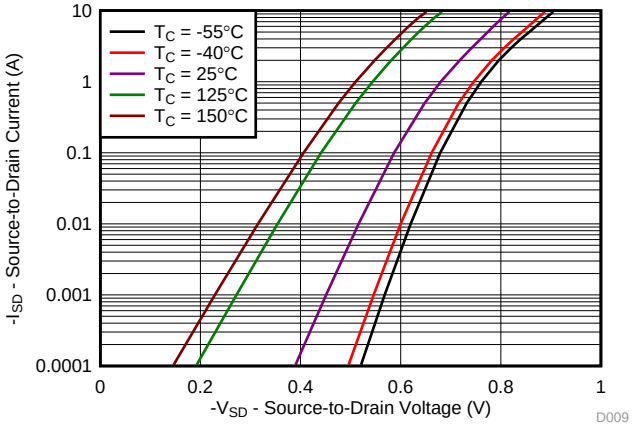
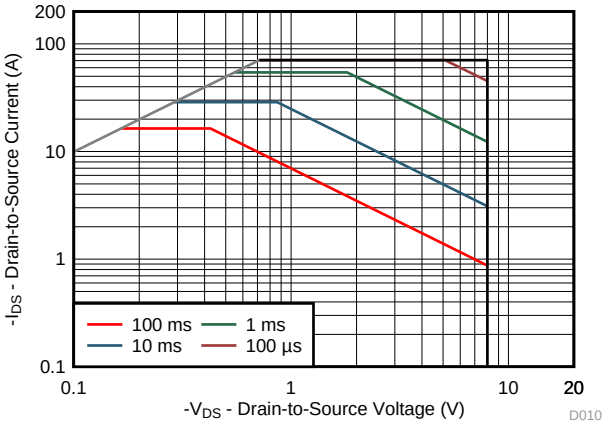


Figure 9. Typical Diode Forward Voltage



Single pulse, typical $R_{\theta JA}$ = 225°C/W

Figure 10. Maximum Safe Operating Area

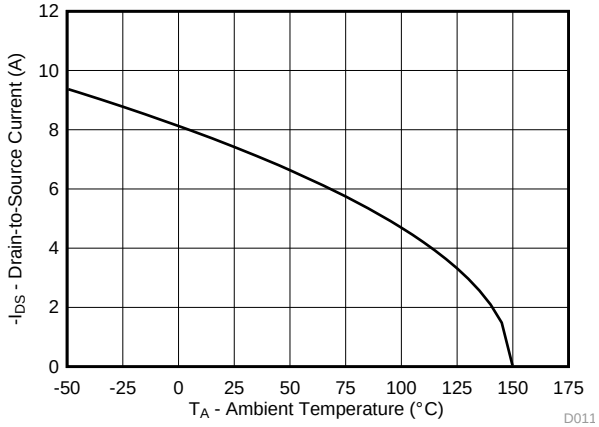


Figure 11. Maximum Drain Current vs Temperature

6 器件和文档支持

6.1 接收文档更新通知

要接收文档更新通知，请导航至 ti.com 上的器件产品文件夹。请单击右上角的*通知我*进行注册，即可收到所有产品更改信息每周摘要。有关更改的详细信息，请查看任何已修订文档中包含的修订历史记录。

6.2 社区资源

下列链接提供到 TI 社区资源的连接。链接的内容由各个分销商“按照原样”提供。这些内容并不构成 TI 技术规范，并且不一定反映 TI 的观点；请参阅 TI 的 《使用条款》。

TI E2E™ 在线社区 ***TI 的工程师对工程师 (E2E) 社区。*** 此社区的创建目的在于促进工程师之间的协作。在 e2e.ti.com 中，您可以咨询问题、分享知识、拓展思路并与同行工程师一道帮助解决问题。

设计支持 ***TI 参考设计支持*** 可帮助您快速查找有帮助的 E2E 论坛、设计支持工具以及技术支持的联系信息。

6.3 商标

NexFET, E2E are trademarks of Texas Instruments.
All other trademarks are the property of their respective owners.

6.4 静电放电警告

这些装置包含有限的内置 ESD 保护。 存储或装卸时，应将导线一起截短或将装置放置于导电泡棉中，以防止 MOS 门极遭受静电损伤。

6.5 Glossary

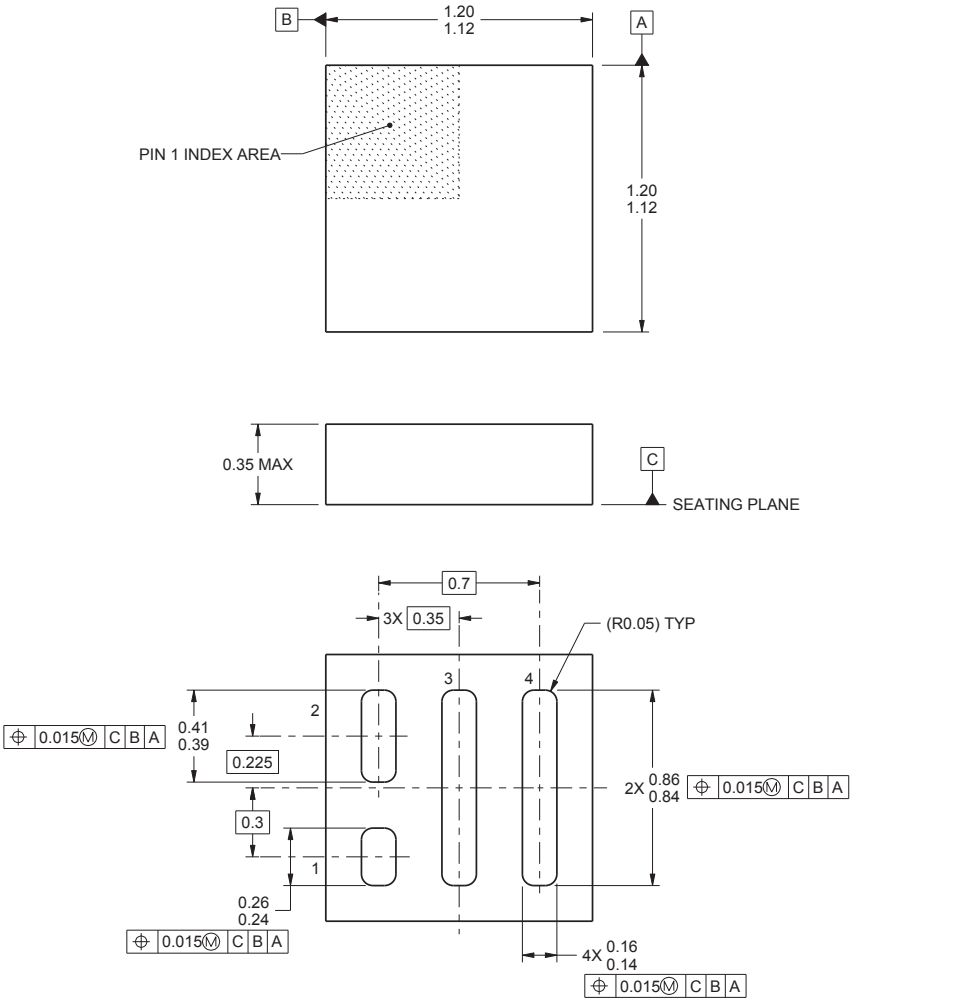
SLYZ022 — *TI Glossary*.

This glossary lists and explains terms, acronyms, and definitions.

7 机械、封装和可订购信息

以下页面包含机械、封装和可订购信息。这些信息是指定器件的最新可用数据。这些数据如有变更，恕不另行通知和修订此文档。如欲获取此数据表的浏览器版本，请参阅左侧的导航。

7.1 CSD22205L 封装尺寸

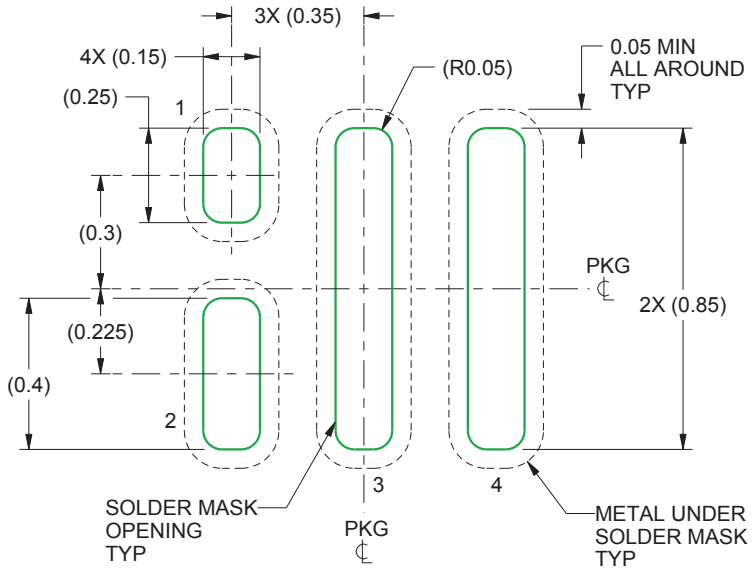


1. 所有线性尺寸的单位均为毫米。括号中的任何尺寸仅供参考。尺寸和公差值符合 ASME Y14.5M 标准。
2. 本图如有变更，恕不另行通知。
3. 此封装为无铅凸点设计。凸点涂料可能有所不同。要确定确切的涂料，请参阅器件数据表或联系当地的 TI 代表。

表 **1.** 引脚配置表

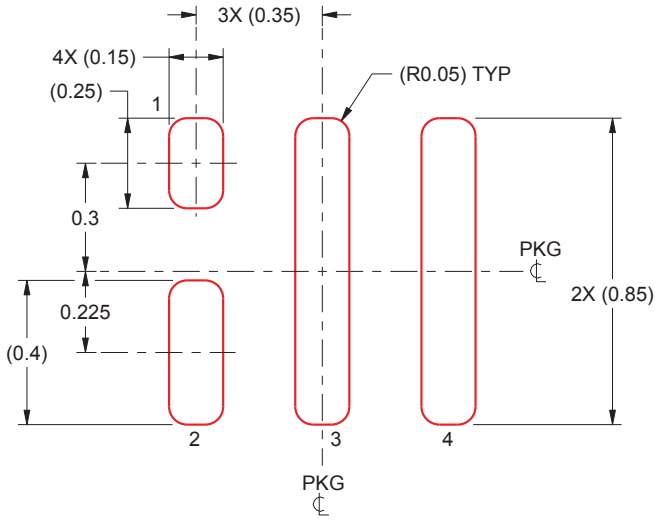
位置	名称
1	栅极
2	漏极
3	源极
4	漏极

7.2 焊盘布局建议



NOTE: 有关更多信息，请参阅*《QFN/SON PCB 连接》*(SLUA271)。

7.3 模版建议



NOTE: 具有漏斗形壁和圆角的激光切割孔可提供更佳的锡膏脱离。IPC-7525 可能提供替代设计建议。

如需了解针对 PCB 设计的建议电路布局，请参阅*《通过 PCB 布局技巧来减少振铃》*(SLPA005)。

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
CSD22205L	ACTIVE	PICOSTAR	YMG	4	3000	RoHS & Green	SNAGCU	Level-1-260C-UNLIM	-55 to 150	205	Samples
CSD22205LT	ACTIVE	PICOSTAR	YMG	4	250	RoHS & Green	SNAGCU	Level-1-260C-UNLIM	-55 to 150	205	Samples

(1) The marketing status values are defined as follows:
ACTIVE: Product device recommended for new designs.
LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.
NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.
PREVIEW: Device has been announced but is not in production. Samples may or may not be available.
OBSOLETE: TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".
RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.
Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

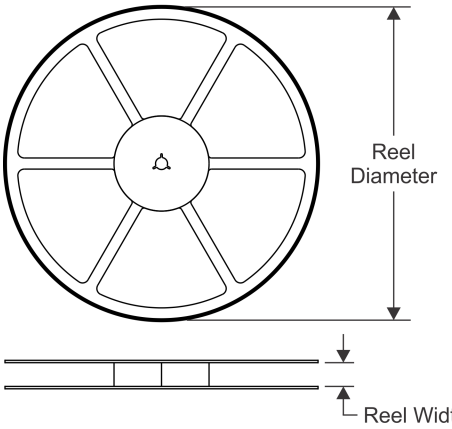
(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

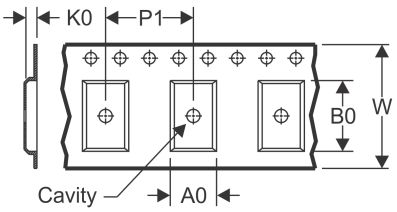
(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

TAPE AND REEL INFORMATION

REEL DIMENSIONS

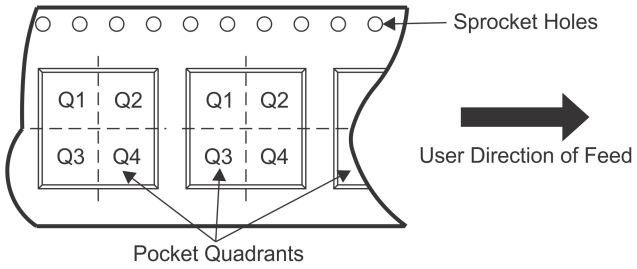


TAPE DIMENSIONS



A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

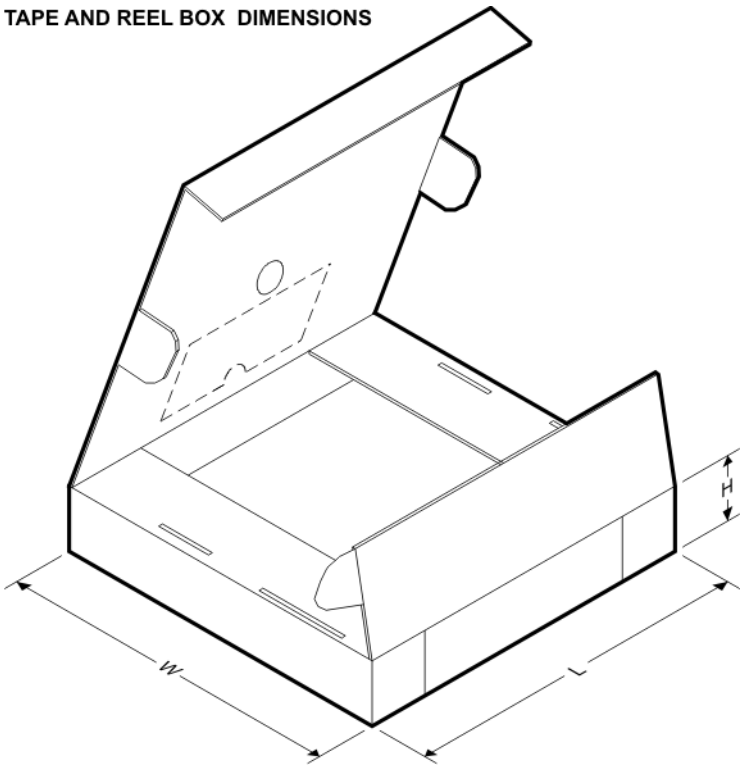
QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
CSD22205L	PICOSTAR	YMG	4	3000	180.0	8.4	1.26	1.26	0.42	4.0	8.0	Q1
CSD22205LT	PICOSTAR	YMG	4	250	180.0	8.4	1.26	1.26	0.42	4.0	8.0	Q1

TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
CSD22205L	PICOSTAR	YMG	4	3000	182.0	182.0	20.0
CSD22205LT	PICOSTAR	YMG	4	250	182.0	182.0	20.0

重要声明和免责声明

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